



CHENMKO ENTERPRISE CO.,LTD
SURFACE MOUNT
Power Management (Dual Transistor)

CHUMF4GP

Tr1:VOLTAGE 12 Volts CURRENT 0.5 Ampere
 DTr2:VOLTAGE 50 Volts CURRENT 100 mAmpere

Halogens free devices

APPLICATION

* Power management circuit

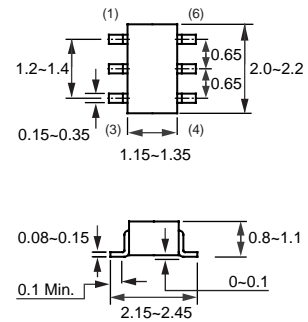
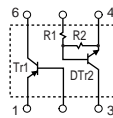
FEATURE

- * Small surface mounting type. (SC-88/SOT-363)
- * Power switching circuit in a single package.
- * Mounting cost and area can be cut in half.
- * Both the 2SA2018 & CHDTC123E in one package.
- * Built in bias resistor(R1=2.2kΩ, Typ.)



SC-88/SOT-363

CIRCUIT



Dimensions in millimeters

SC-88/SOT-363

2SA2018 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	Collector-base voltage		-	-15	V
V _{CEO}	Collector-emitter voltage		-	-12	V
V _{EBO}	Emitter-base voltage		-	-6	V
I _C	DC Output current		-	-500	mA
I _{CP}		NOTE.1	-	-1000	
P _c	power dissipation	NOTE.2	-	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		-	150	°C

Note

1. Single Pulse Pw=1ms
2. 120mW per element must not be exceeded
Each terminal mounted on a recommended land.

CHDTC123E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	Supply voltage		–	50	V
V _{IN}	Input voltage		-10	+20	V
I _O	DC Output current		–	100	mA
I _{C(Max.)}		NOTE.1	–	100	
P _C	Power dissipation	NOTE.2	–	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		–	150	°C

Note

1. Characteristics of built-in transistor.
2. Each terminal mounter on a recommended land.

2SA2018 CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BV _{CEO}	Collector-emitter breakdown voltage	I _C =-1mA	-12	–	–	V
BV _{CBO}	Collector-base breakdown voltage	I _C =-10uA	-15	–	–	V
BV _{EBO}	Emitter-base breakdown voltage	I _E =-10uA	-6	–	–	V
I _{CBO}	Collector cut-off current	V _{CB} =-15V	–	–	-100	nA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V	–	–	-100	nA
h _{FE}	DC current gain	V _{CE} =-2V, I _C =-10mA	270	–	680	–
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-200mA, I _B =-10mA	–	-100	-250	mV
C _{ob}	Collector output capacitance	V _{CB} =-10V, I _E =0mA, f=1MHZ	–	6.5	–	pF
f _T	Transition frequency	V _{CE} =-2V, I _E =10mA, f=100MHZ	–	260	–	MHz

Note

1. Pulse test: t_p≤300uS; δ≤0.02.

CHDTC123E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{I(off)}	Input off voltage	I _O =100uA; V _{CC} =5.0V	0.5	–	–	V
V _{I(on)}	Input on voltage	I _O =20mA; V _O =0.3V	–	–	3.0	V
V _{O(on)}	Output voltage	I _O =10mA; I _I =0.5mA	–	0.1	0.3	V
I _I	Input current	V _I =5V	–	–	3.8	mA
I _{C(off)}	Output current	V _I =0V; V _{CC} =50V	–	–	0.5	uA
G ₁	DC current gain	I _O =20mA; V _O =5.0V	20	–	–	–
R ₁	Input resistor		1.54	2.2	2.86	KΩ
R _{2/R₁}	Resistor ratio		0.8	1.0	1.2	–
f _T	Transition frequency	I _E =-5mA, V _{CE} =10.0V f=100MHz	–	250	–	MHz

Note

- Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHUMF4GP)

2SA2018 Typical Electrical Characteristics

Fig.1 Ground emitter propagation characteristics

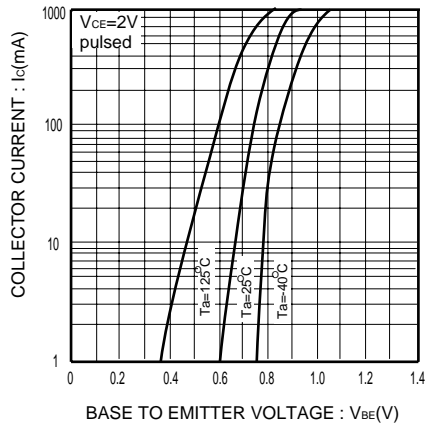


Fig.2 DC current gain vs. collector current

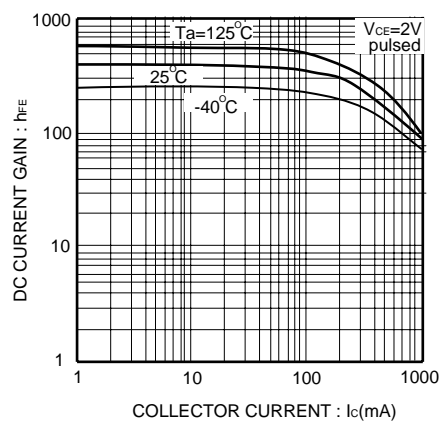


Fig.3 Collector-emitter saturation voltage vs. collector current (I)

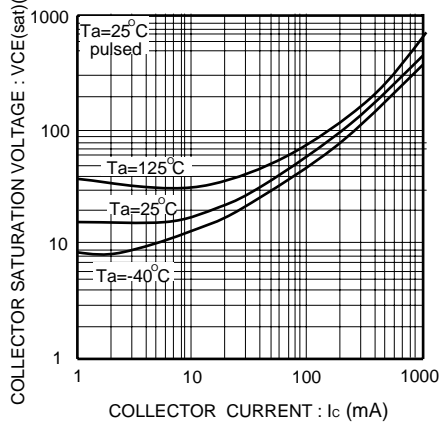
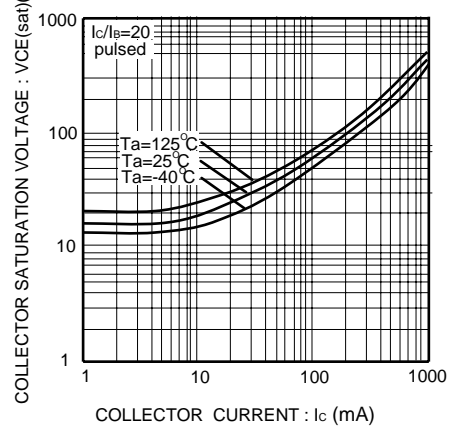


Fig.4 Collector-emitter saturation voltage vs. collector current (II)



RATING CHARACTERISTIC CURVES (CHUMF4GP)

2SA2018 Typical Electrical Characteristics

Fig.5 Base-emitter saturation voltage vs. collector current

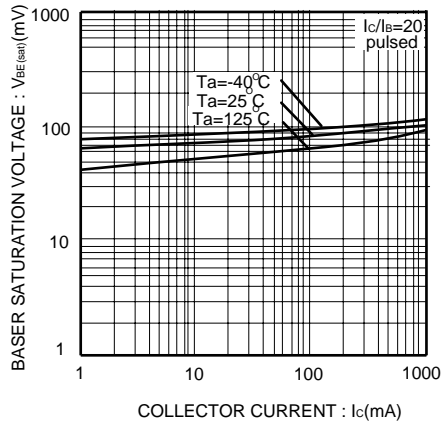


Fig.6 Gain bandwidth product vs. collector current

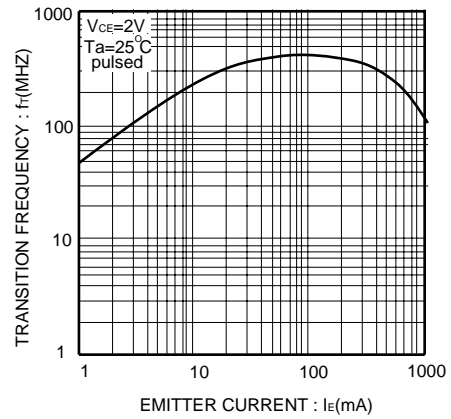
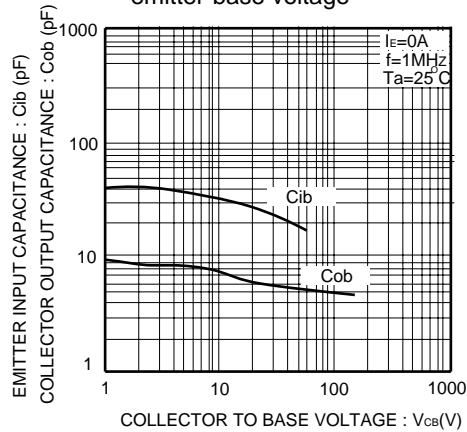


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage



RATING CHARACTERISTIC CURVES (CHUMF4GP)

CHDTC123E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

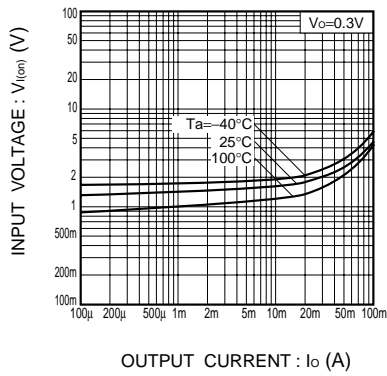


Fig.2 Output current vs. input voltage (OFF characteristics)

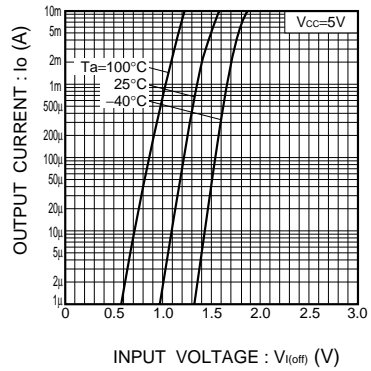


Fig.3 DC current gain vs. output current

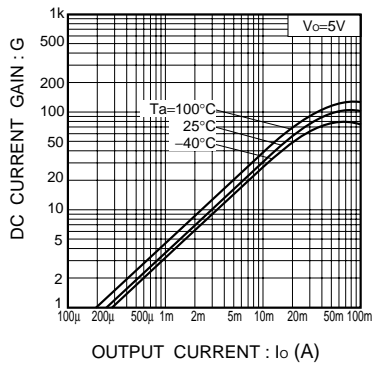


Fig.4 Output voltage vs. output current

